Post Ion Implanted Photoresist Stripping Using Supercritical Carbon Dioxide

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High does ion implanted photoresit(HDIPR) was stripped off from the surface of semiconductor wafers using supercritical carbon dioxide(SCCO$_2$) and additives Fluorinated srfactants and alcohols were add to enhance the solvation effect. We investigated different surfactant concentrations, stripping temperatures and pressure, and magnetic stirring and their impact on the process efficiency. The wafer surface was analyzed before and after stripping by scanning microscopy and by energy dispersive X-ray spectrometer. The result indicate that HDIPR could be stripped completely in 30 min using a Surfactant+co solvent mixture at 20Mpa and 343K.